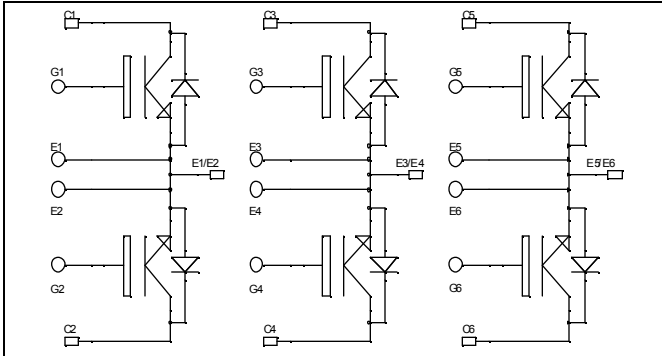


**Triple Dual Common Source  
Trench + Field Stop IGBT®  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 50A @ T_c = 80^\circ C$**

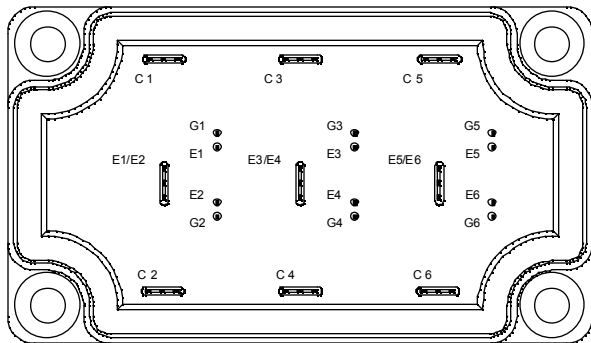


### Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

### Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration



### Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of  $V_{CESat}$
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	80
		$T_C = 80^\circ C$	50
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	100
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	176
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	100A @ 550V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu\text{A}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			600	nA

## Dynamic Characteristics

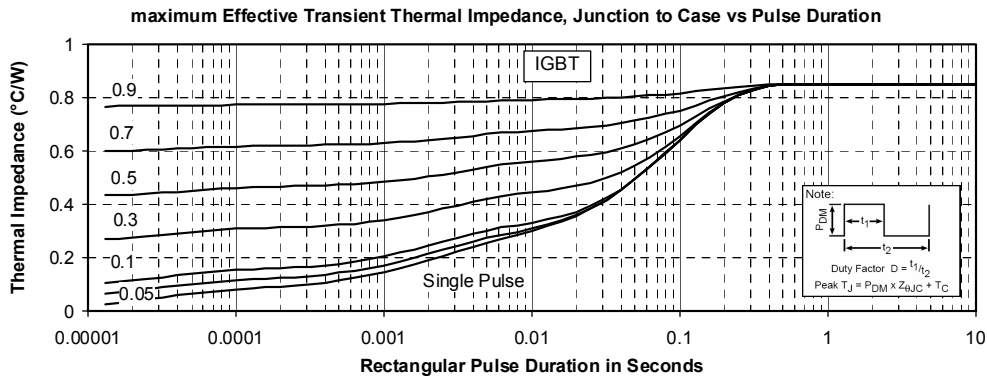
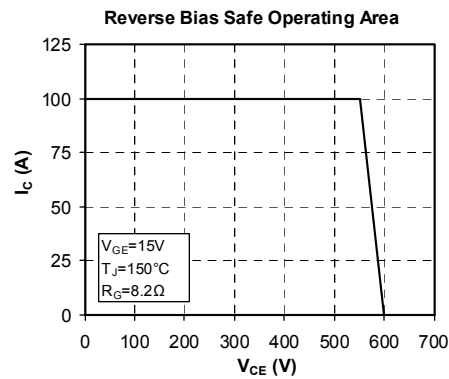
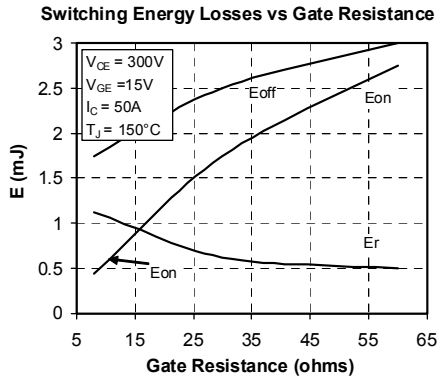
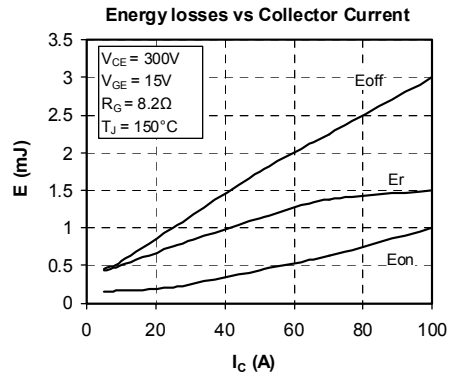
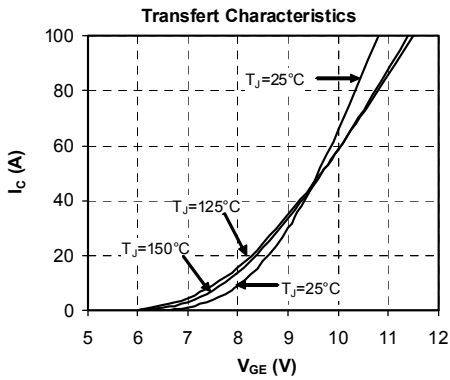
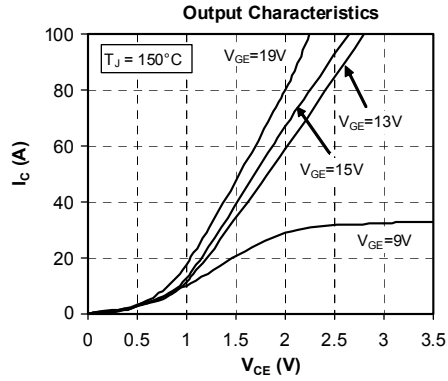
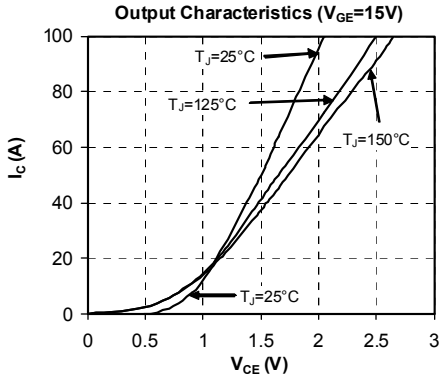
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}$		3150		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25\text{V}$		200		
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		95		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 50\text{A}$ $R_G = 8.2\Omega$		110		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
$T_f$	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 50\text{A}$ $R_G = 8.2\Omega$		120		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
$T_f$	Fall Time			60		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 50\text{A}$	$T_j = 25^\circ\text{C}$	0.3		mJ
			$T_j = 150^\circ\text{C}$	0.43		
$E_{off}$	Turn-off Switching Energy	$R_G = 8.2\Omega$	$T_j = 25^\circ\text{C}$	1.35		mJ
			$T_j = 150^\circ\text{C}$	1.75		

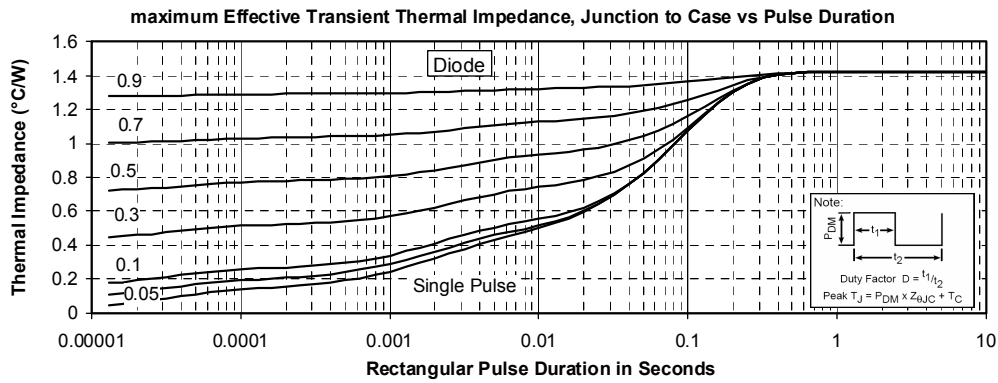
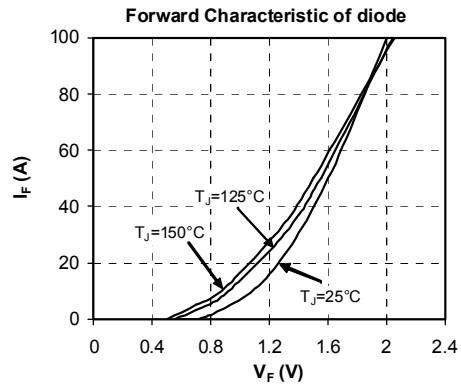
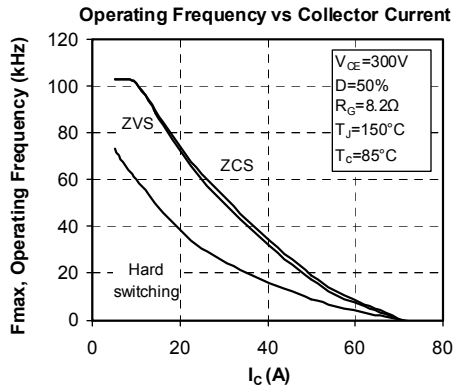
## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	$\mu\text{A}$
			$T_j = 150^\circ\text{C}$		500	
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	50		A
$V_F$	Diode Forward Voltage	$I_F = 50\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
$t_{rr}$	Reverse Recovery Time	$I_F = 50\text{A}$ $V_R = 300\text{V}$ $di/dt = 1800\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		ns
			$T_j = 150^\circ\text{C}$	150		
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	2.6		$\mu\text{C}$
			$T_j = 150^\circ\text{C}$	5.4		
$E_r$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	0.6		mJ
			$T_j = 150^\circ\text{C}$	1.2		



## Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.